

CLAIMS

1. A resist material comprising:

(A) an organic solvent,

(B) a resin which exhibits transmittance of 30%/μm or greater at a wavelength of 193 nm, is an alkali insoluble or alkali sparingly soluble resin protected with an acid labile group, and has an alicyclic structure having a - (CO)-O-(CO)_k- group (in which, k stands for 0 or 1) which becomes alkali soluble upon dissociation of said acid labile group,

(C) a photoacid generator,

(D) a basic compound, and

(E) at least one compound selected from the group consisting of thiol derivatives, disulfide derivatives and thiolsulfonate derivatives.

2. A resist material of Claim 1, wherein the thiol derivatives are each free of a carbon-carbon double bond.

3. A resist material of Claim 1, further comprising (F) a dissolution inhibitor.

4. A resist material of Claim 2, further comprising (F) a dissolution inhibitor.

5. A resist material according to Claim 1, further comprising (G) a surfactant.

6. A resist material according to Claim 2, further comprising (G) a surfactant.

7. A resist material according to Claim 3, further comprising (G) a surfactant.

8. A resist material according to Claim 4, further comprising (G) a surfactant.

9. A pattern forming method, which comprises steps of applying a resist material according to Claim 1 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

10. A pattern forming method, which comprises steps of applying a resist material according to Claim 2 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

11. A pattern forming method, which comprises steps of applying a resist material according to Claim 3 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

12. A pattern forming method, which comprises steps of applying a resist material according to Claim 4 onto a substrate; after a heat treatment, exposing the resist

material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

13. A pattern forming method, which comprises steps of applying a resist material according to Claim 5 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

14. A pattern forming method, which comprises steps of applying a resist material according to Claim 6 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

15. A pattern forming method, which comprises steps of applying a resist material according to Claim 7 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

16. A pattern forming method, which comprises steps of applying a resist material according to Claim 8 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a

photomask; and after an optional heat treatment, developing the resist material with a developer.